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(54) **SOLID-STATE IMAGE SENSOR, METHOD OF MANUFACTURING THE SAME AND CAMERA**

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H01L 31/18 (2006.01)

(52) **U.S. Cl.**

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(58) **Field of Classification Search**

CPC H04N 5/374; H01L 31/0232
See application file for complete search history.

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Primary Examiner — James Hannett

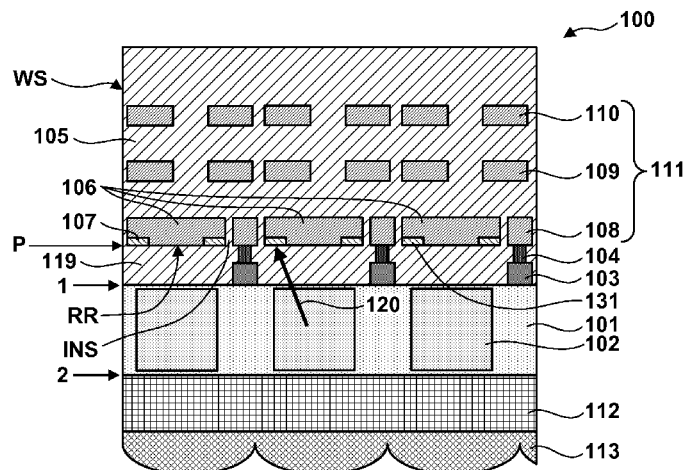
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(57)

ABSTRACT

An image sensor includes a semiconductor layer having first and second faces, and a wiring structure arranged on a side of the first face, wherein photoelectric converters are arranged in the semiconductor layer and light is incident on the second face. The wiring structure includes reflection portions having reflection regions and arranged for at least some of the photoelectric converters, absorbing portions arranged around the reflection regions, an insulator portion arranged to surround the absorbing portions, and an inter-layer insulating film arranged between the first face and a group of the reflection portions, the light absorbing portions, and the insulator portion, and a reflectance of the light absorbing portions is smaller than a reflectance of the reflection regions, and a light transmittance of the light absorbing portions is smaller than a light transmittance of the insulator portion.

17 Claims, 11 Drawing Sheets



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FIG. 1

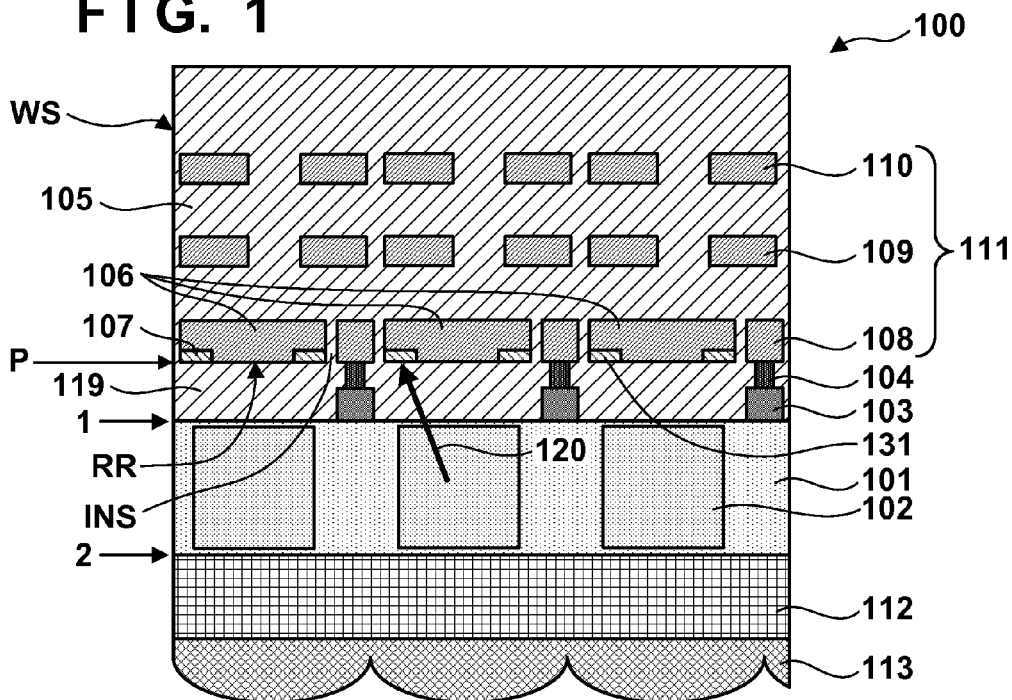


FIG. 2

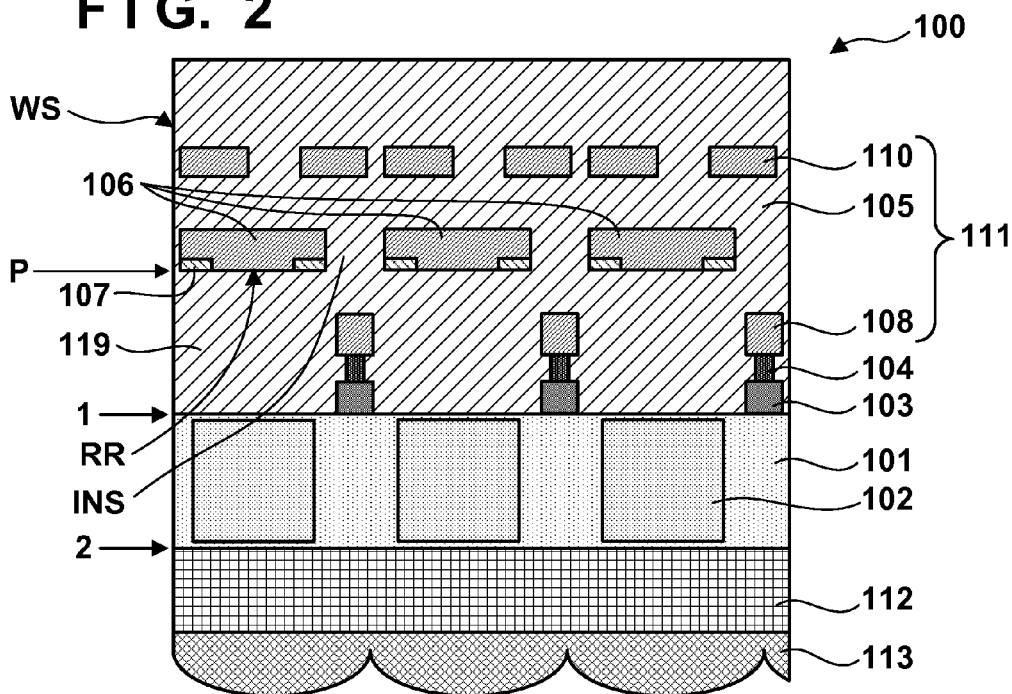


FIG. 3

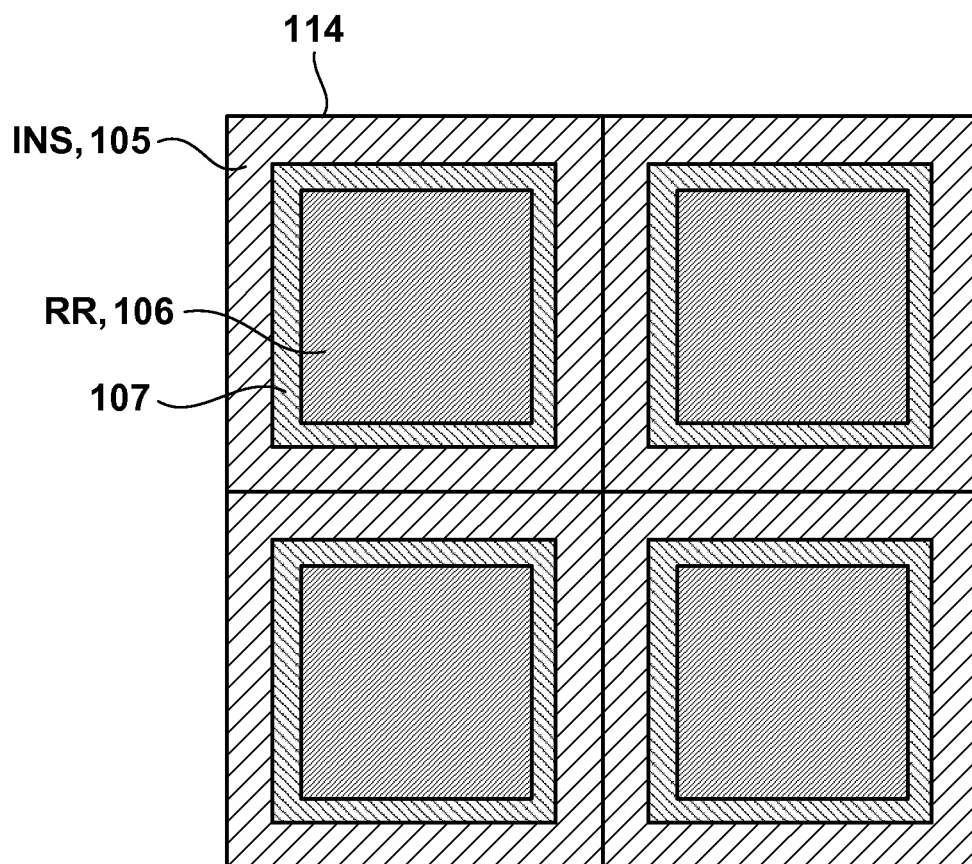


FIG. 4

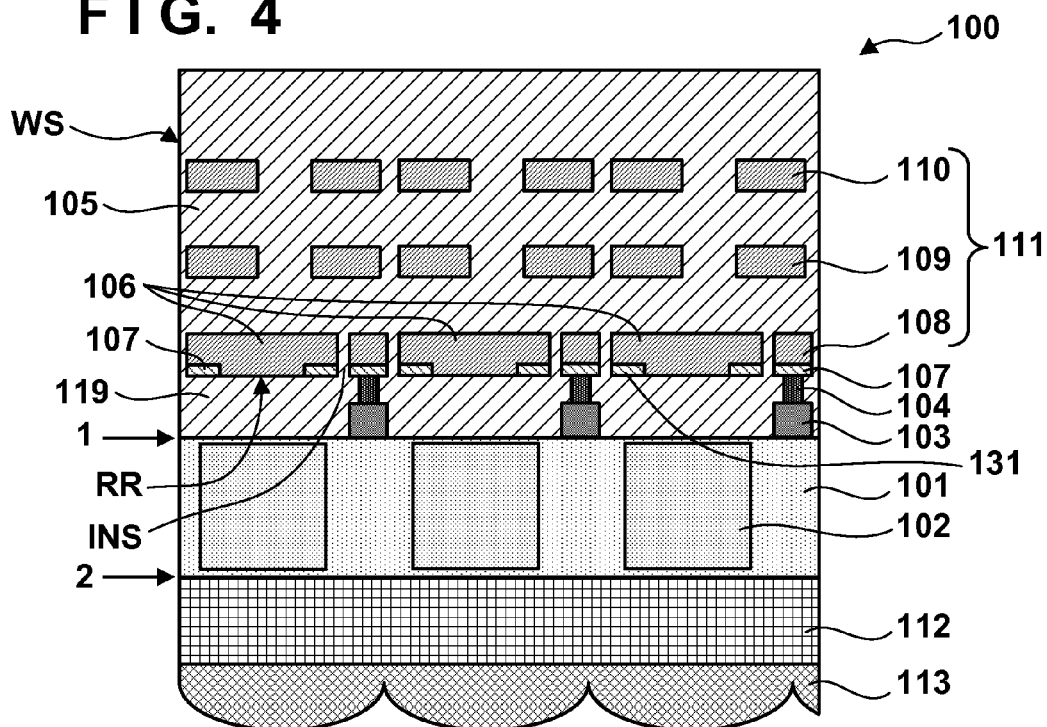


FIG. 5

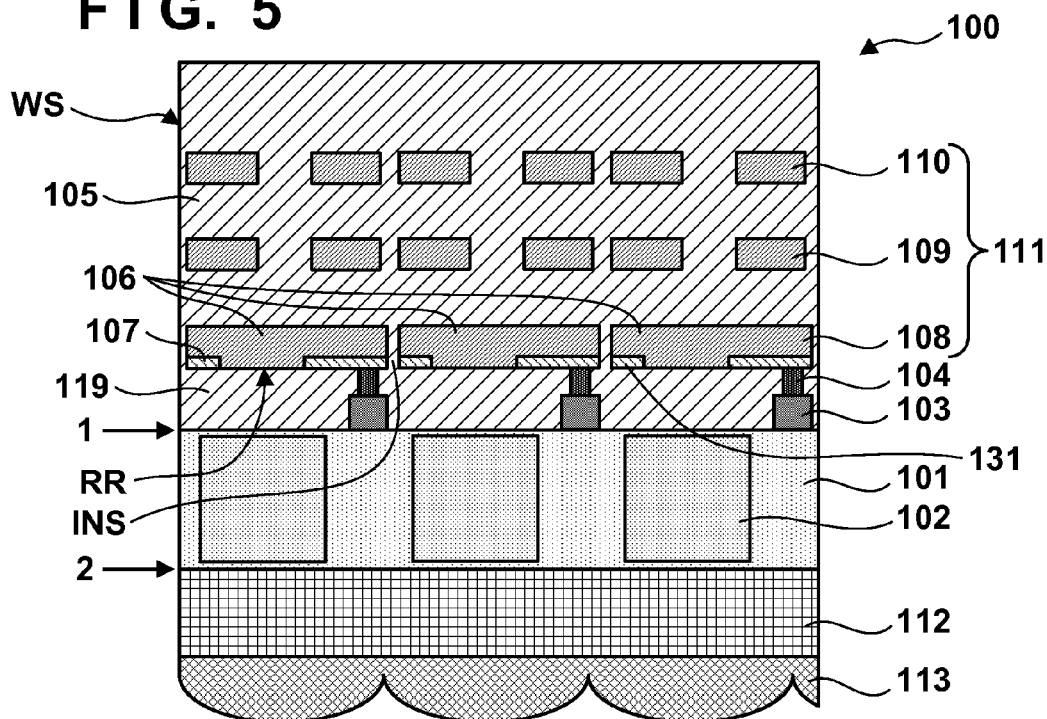


FIG. 6A

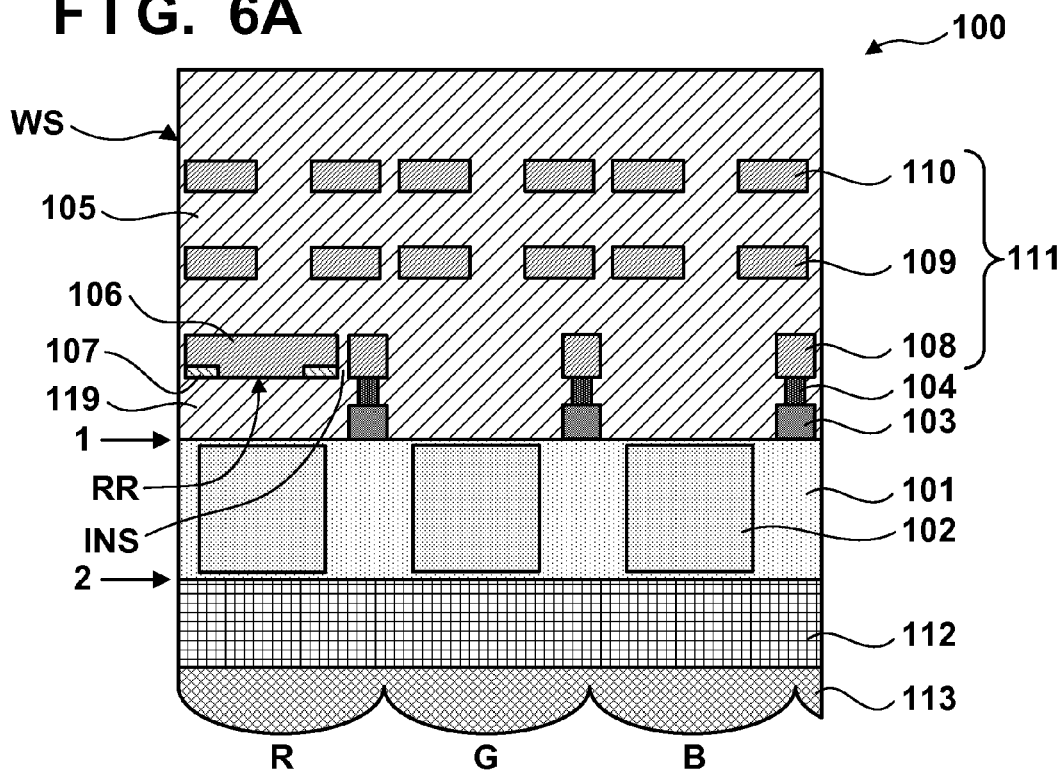


FIG. 6B

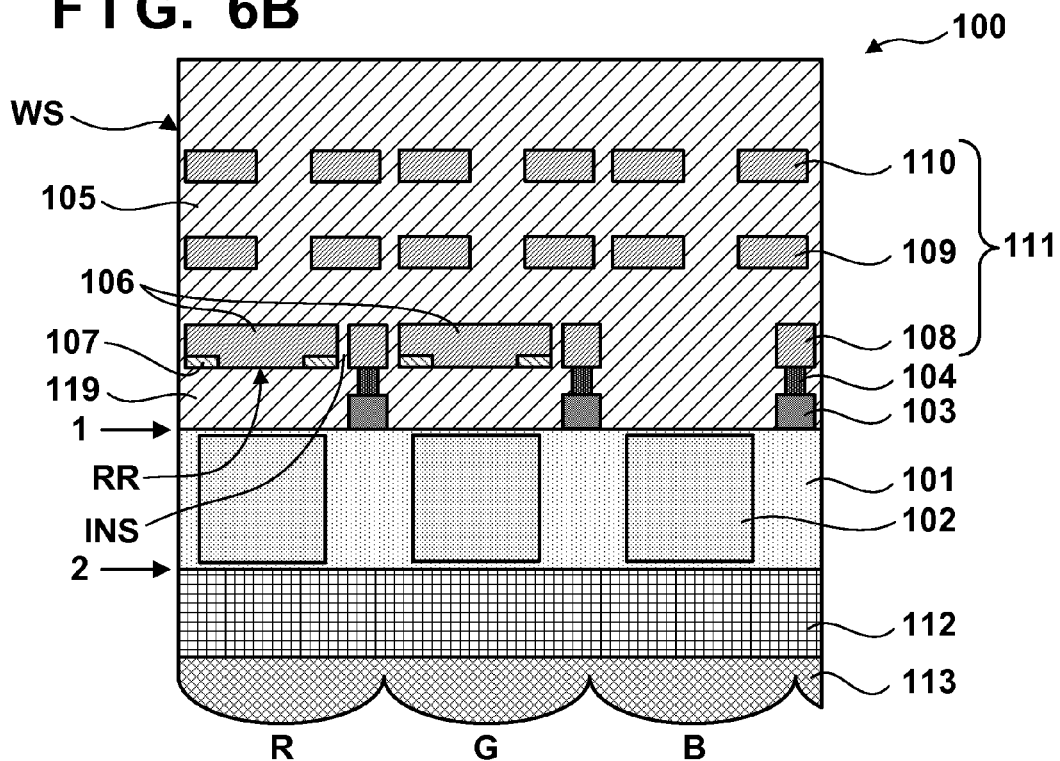


FIG. 7

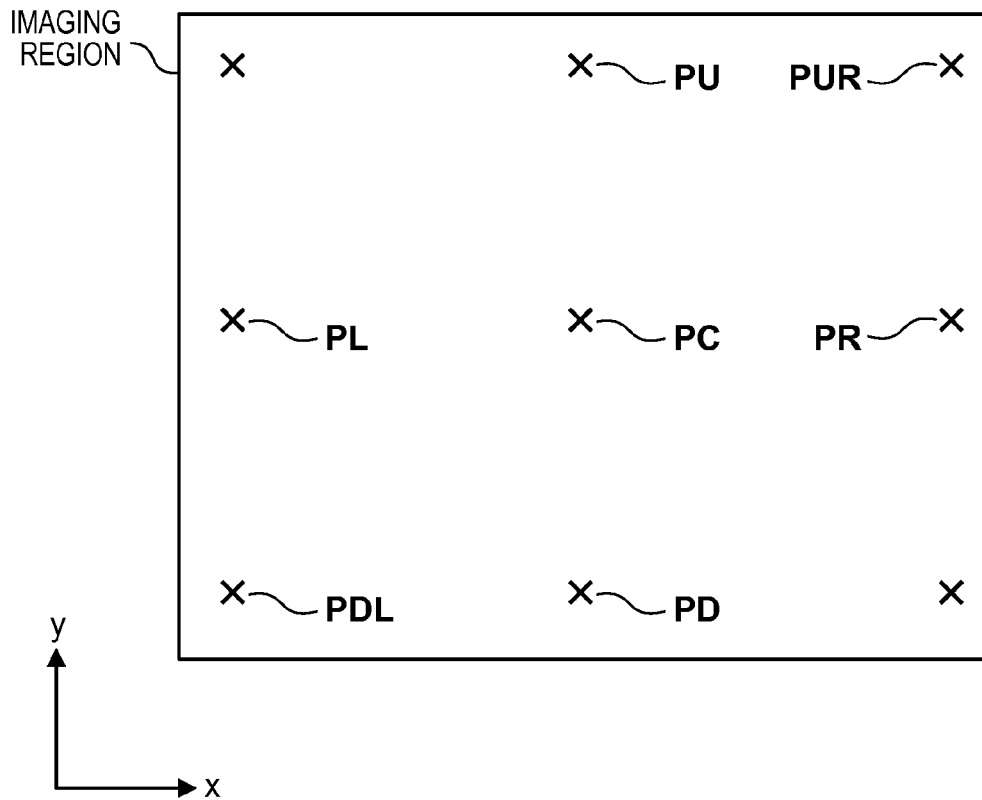


FIG. 8A

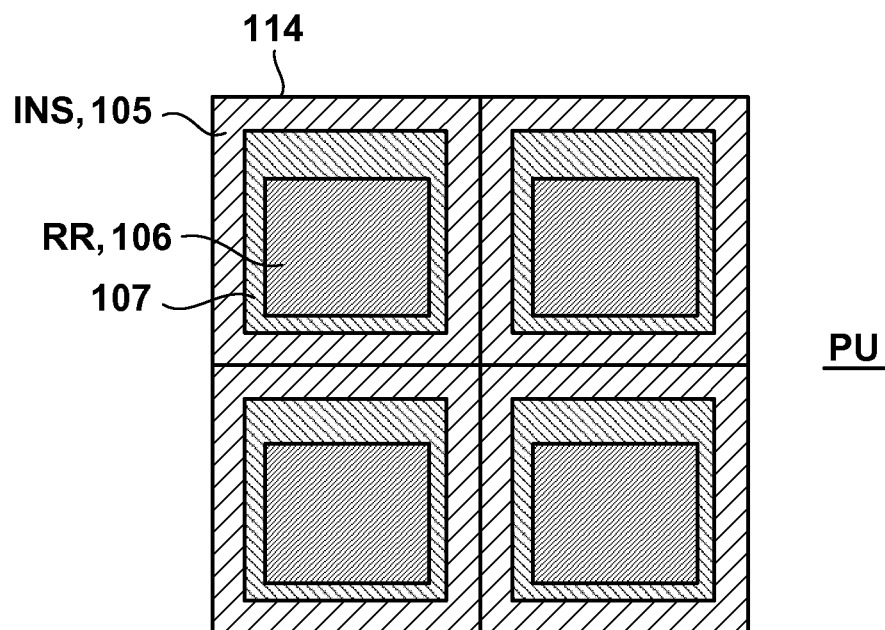
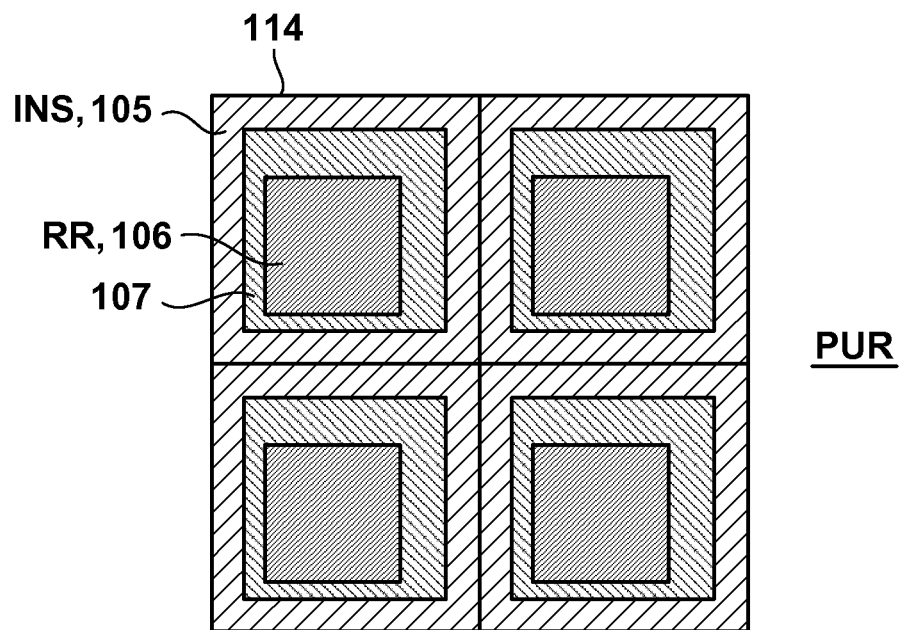


FIG. 8B



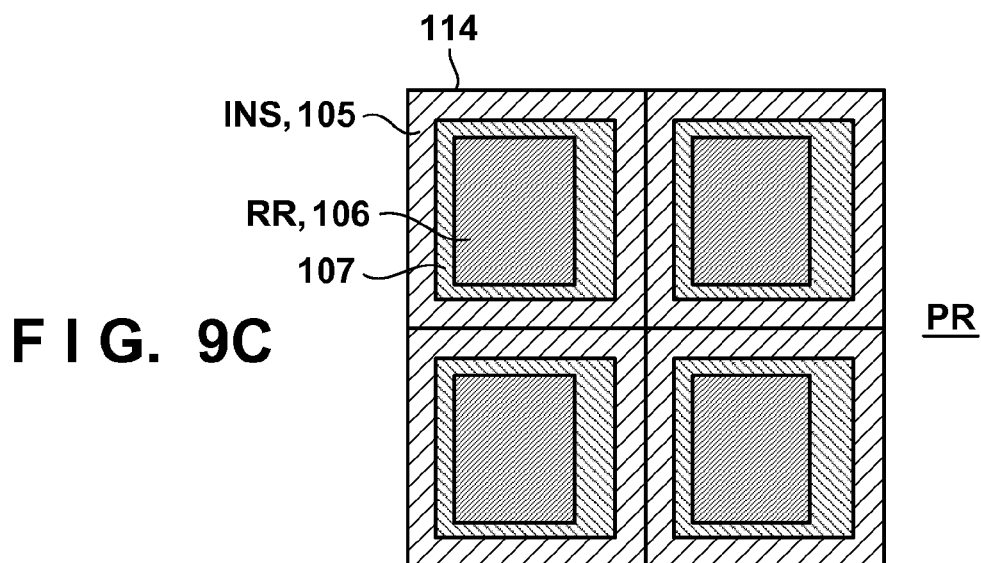
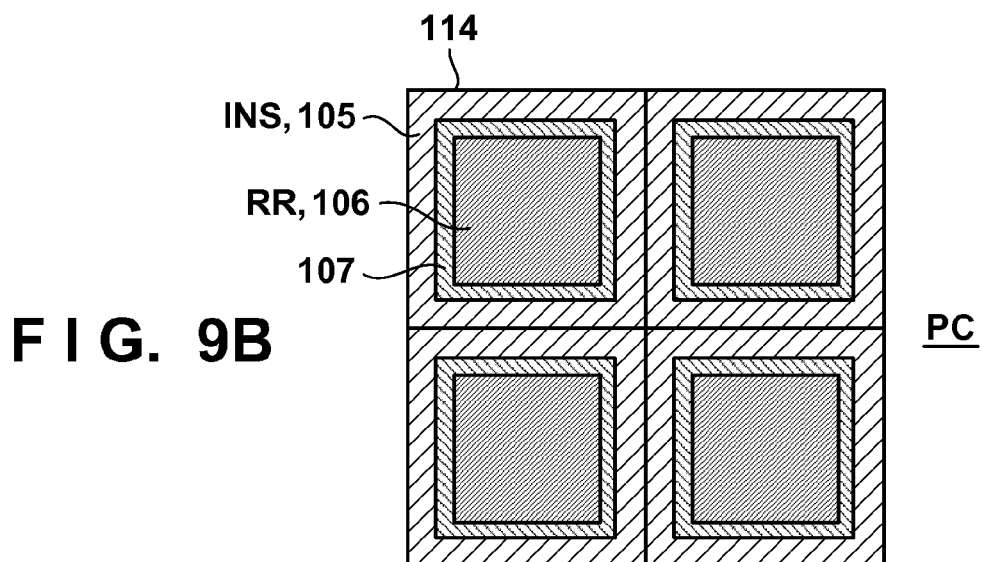
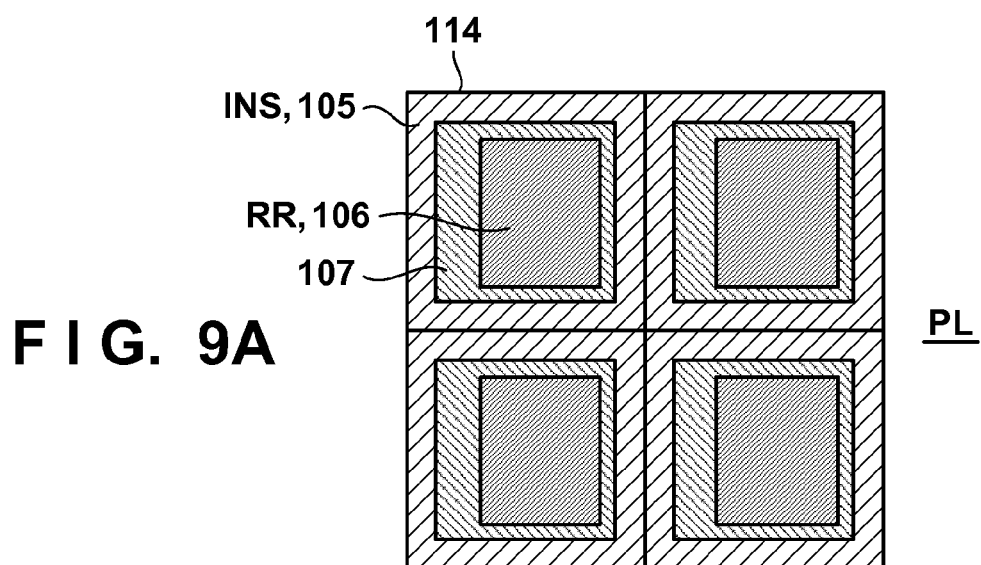


FIG. 10A

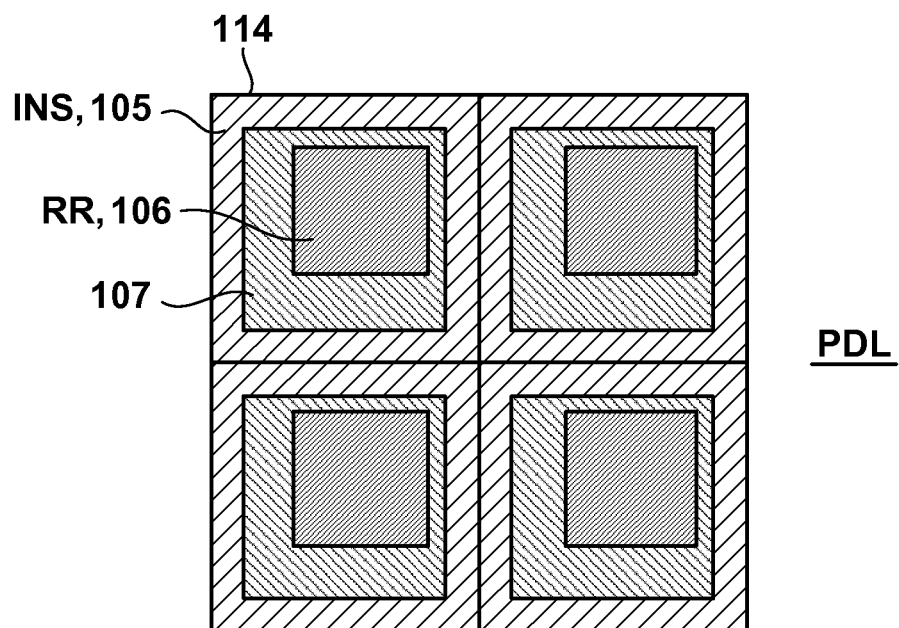


FIG. 10B

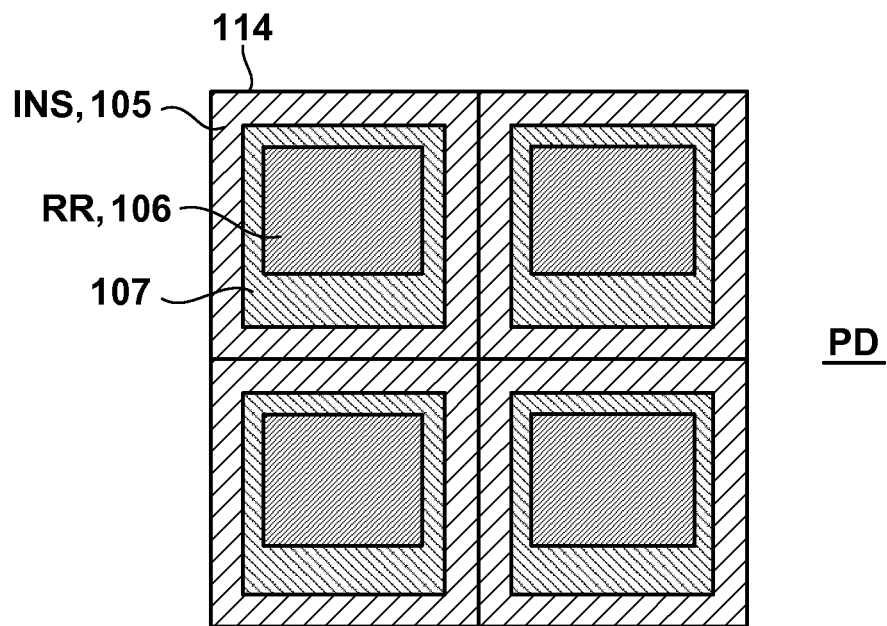


FIG. 11A

PL

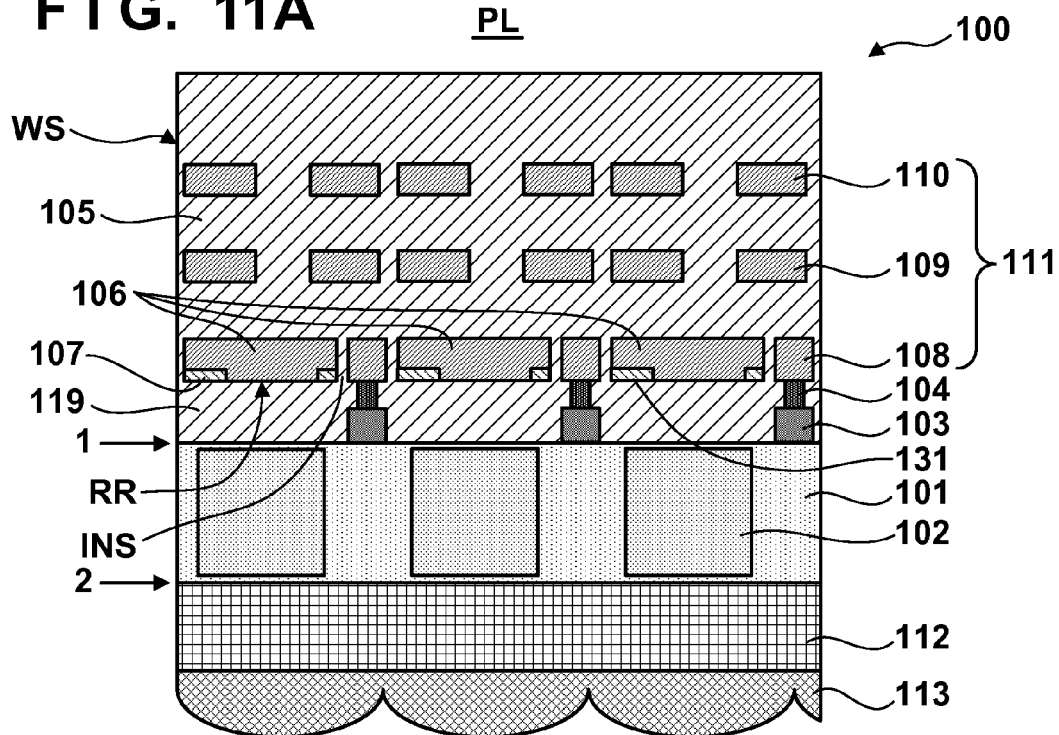


FIG. 11B

PR

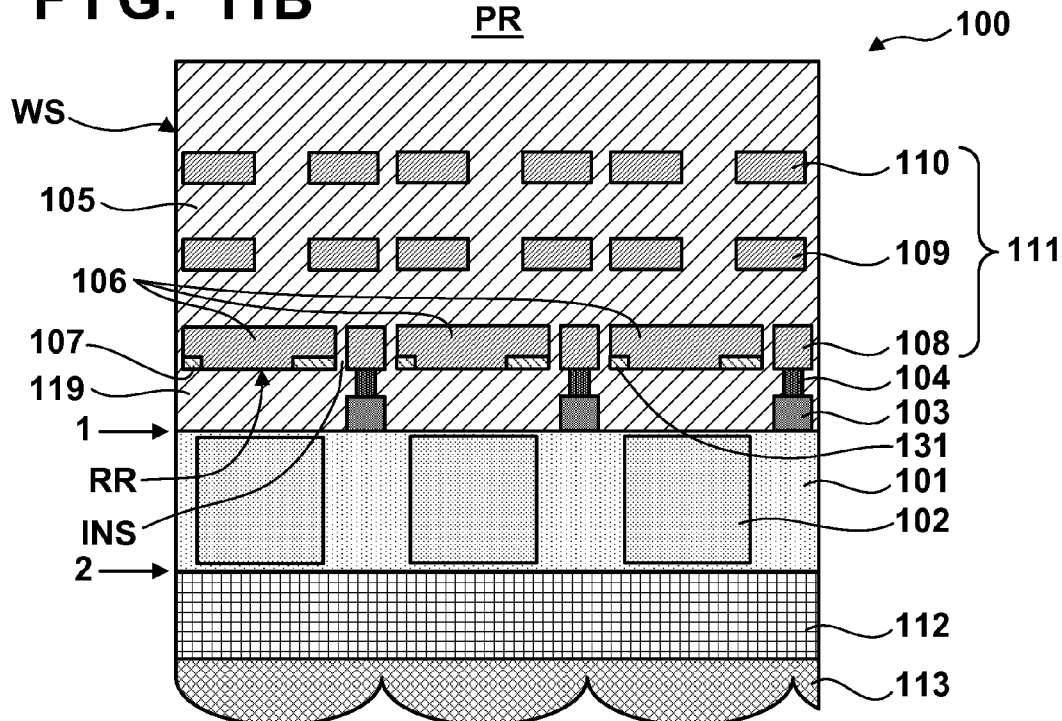


FIG. 12A

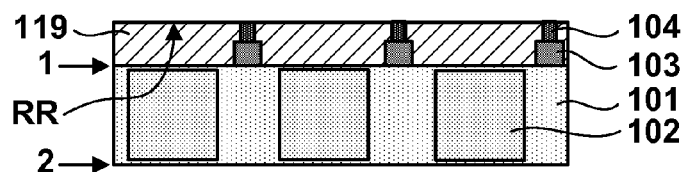


FIG. 12B

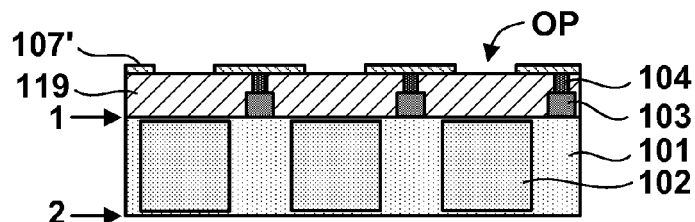


FIG. 12C

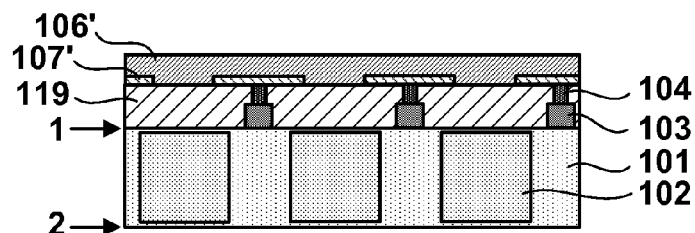


FIG. 12D

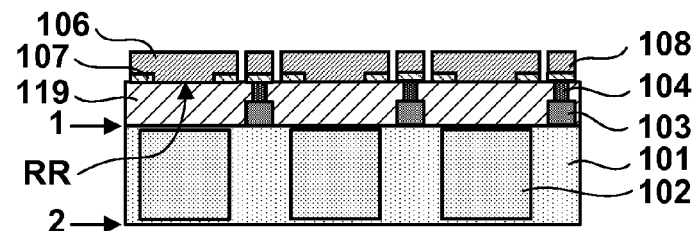


FIG. 12E

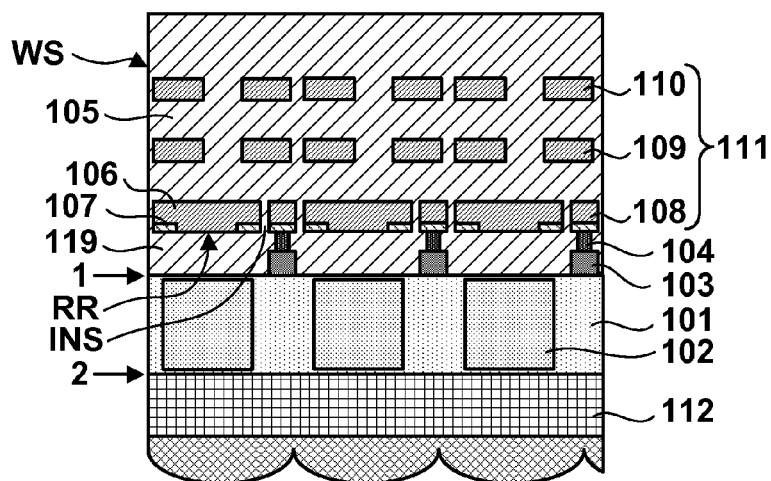
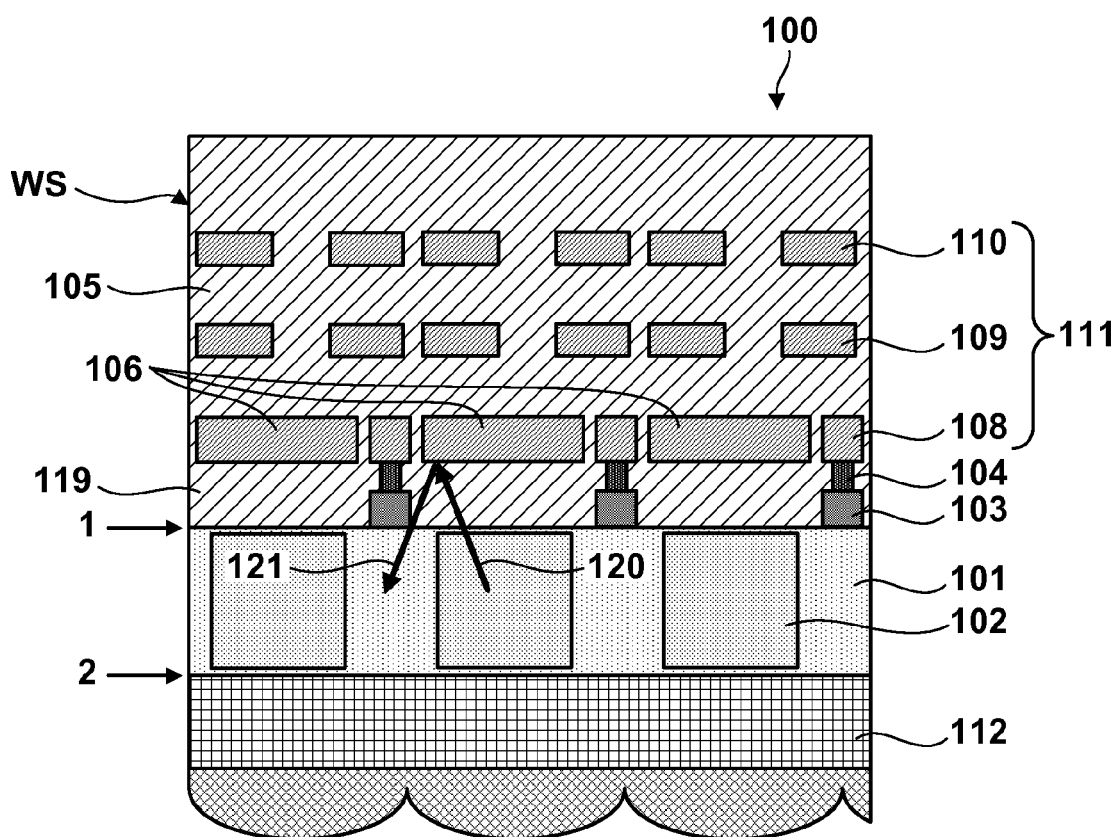


FIG. 13



SOLID-STATE IMAGE SENSOR, METHOD OF MANUFACTURING THE SAME AND CAMERA

This application is a continuation of pending application Ser. No. 14/064,453, filed Oct. 28, 2013, which has been allowed.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a solid-state image sensor, a method of manufacturing the same, and a camera.

2. Description of the Related Art

It has been required to improve the sensitivity of a solid-state image sensor used in a digital video camera, digital still camera, and the like. Japanese Patent Laid-Open No. 2011-151420 discloses a so-called back-side illumination solid-state image sensor. In the back-side illumination solid-state image sensor, if a semiconductor layer has a thickness of, for example, several μm or smaller, long-wavelength components of incident light having passed through a microlens pass through the semiconductor layer without being sufficiently absorbed. According to Japanese Patent Laid-Open No. 2011-151420, a reflection layer for returning, to the semiconductor layer, light having passed through the semiconductor layer is provided on the whole surface on the wiring layer side of the semiconductor layer. It is possible to improve the sensitivity by returning light having passed through the semiconductor layer to a photoelectric converter included in the semiconductor layer.

In the arrangement in which the reflection layer is provided on the whole surface on the wiring layer side of the semiconductor layer, however, color mixing may occur. More specifically, light which has passed through a first pixel and then obliquely entered a portion of the reflection layer between the first pixel and a second pixel adjacent to it may be reflected by that portion to enter the second pixel. In this case, light which should be detected in the first pixel is actually detected in the second pixel, thereby causing color mixing.

SUMMARY OF THE INVENTION

The present invention provides a technique advantageous in reducing color mixing.

The first aspect of the present invention provides a solid-state image sensor comprising: a semiconductor layer having a first face and a second face; and a wiring structure arranged on a side of the first face, wherein a plurality of photoelectric converters are arranged in the semiconductor layer, wherein light from an object is incident on the second face, wherein the wiring structure includes: a plurality of reflection portions arranged for at least some of the plurality of photoelectric converters, each of the plurality of reflection portions having a reflection region; a plurality of light absorbing portions each of which is arranged around the reflection region of corresponding one of the plurality of reflection portions; an insulator portion arranged to surround each of the plurality of light absorbing portions; and an interlayer insulating film arranged between the first face and a group of the plurality of reflection portions, the plurality of light absorbing portions, and the insulator portion, and wherein a reflectance of each of the plurality of light absorbing portions is smaller than a reflectance of the reflection region of corresponding one of the reflection

portions, and a light transmittance of each of the plurality of light absorbing portions is smaller than a light transmittance of the insulator portion.

The second aspect of the present invention provides a method of manufacturing a solid-state image sensor which includes a semiconductor layer having a first face and a second face, and a wiring structure arranged on a side of the first face, wherein a plurality of photoelectric converters are arranged in the semiconductor layer, wherein light from an object is incident on the second face, wherein the wiring structure includes a plurality of reflection portions which are arranged for at least some of the plurality of photoelectric converters, each of the plurality of reflection portions having a reflection region, a plurality of light absorbing portions each of which is arranged around the reflection region of corresponding one of the plurality of reflection portions, an insulator portion which is arranged to surround each of the plurality of light absorbing portions, and an interlayer insulating film which is arranged between the first face and a group of the plurality of reflection portions, the plurality of light absorbing portions, and the insulator portion, and wherein a reflectance of each of the plurality of light absorbing portions is smaller than a reflectance of the reflection region of corresponding one of the reflection portions, and a light transmittance of each of the plurality of light absorbing portions is smaller than a light transmittance of the insulator portion, and the method comprising the steps of: forming the interlayer insulating film on the first face of the semiconductor layer, forming the plurality of light absorbing portions and the plurality of reflection portions on the interlayer insulating film, and forming the insulator portion to surround each of the plurality of light absorbing portions.

The third aspect of the present invention provides a camera comprising: the solid-state image sensor as specified as the first aspect of the present invention; and a processor which processes a signal output from the solid-state image sensor.

Further features of the present invention will become apparent from the following description of exemplary embodiments with reference to the attached drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a sectional view schematically showing the sectional structure of a solid-state image sensor according to the first embodiment of the present invention;

FIG. 2 is a sectional view schematically showing the sectional structure of the solid-state image sensor according to the first embodiment of the present invention;

FIG. 3 is a sectional view showing a wiring structure taken along a virtual plane P shown in FIG. 1;

FIG. 4 is a sectional view schematically showing the sectional structure of the solid-state image sensor according to the first embodiment of the present invention;

FIG. 5 is a sectional view schematically showing the sectional structure of a solid-state image sensor according to the second embodiment of the present invention;

FIGS. 6A and 6B are sectional views each schematically showing the sectional structure of a solid-state image sensor according to the third embodiment of the present invention;

FIG. 7 is a view for explaining the fourth embodiment of the present invention;

FIGS. 8A and 8B are views for explaining the fourth embodiment of the present invention;

FIGS. 9A to 9C are views for explaining the fourth embodiment of the present invention;

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FIGS. 10A and 10B are views for explaining the fourth embodiment of the present invention;

FIGS. 11A and 11B are views for explaining the fourth embodiment of the present invention;

FIGS. 12A to 12E are views exemplifying a method of manufacturing the solid-state image sensor according to the first embodiment of the present invention; and

FIG. 13 is a view showing a comparative example.

DESCRIPTION OF THE EMBODIMENTS

FIG. 1 schematically shows the sectional structure of a solid-state image sensor 100 according to the first embodiment of the present invention. Note that FIG. 1 shows only three pixels but the solid-state image sensor 100 can include a larger number of pixels. The solid-state image sensor 100 can include a semiconductor layer 101 having a first face 1 and second face 2, a plurality of photoelectric converters 102 two-dimensionally arranged in the semiconductor layer 101, and a wiring structure WS arranged on the side of the first face 1. The solid-state image sensor 100 is configured so that light from an object is incident on the second face 2 through an imaging lens. That is, the solid-state image sensor 100 is formed as a back-side illumination solid-state image sensor in which a wiring structure is arranged on the side of the first face of a semiconductor layer and light from an object is incident on the second face of the semiconductor layer. A plurality of microlenses 113 can be typically arranged on the side of the second face 2. A planarizing layer 112 can be arranged between the second face 2 of the semiconductor layer 101 and the microlenses 113. Although not shown, a color filter layer can be arranged between the planarizing layer 112 and the microlenses 113.

The semiconductor layer 101 can be made of, for example, silicon. The plurality of photoelectric converters 102 are two-dimensionally arranged in the semiconductor layer 101. As an example, the semiconductor layer 101 can have a semiconductor region of a first conductivity type, and the photoelectric converter 102 can include a semiconductor region of a second conductivity type arranged within the semiconductor region of the first conductivity type. Note that the first and second conductivity types are opposite to each other. One pixel typically includes one photoelectric converter 102. Pixels or elements included in the pixels are electrically isolated from each other by an isolation portion. The isolation portion can include an insulator such as LOCOS (LOCAl Oxidation of Silicon) or STI (Shallow Trench Isolation). Alternatively, the isolation portion may include an insulator extending through the semiconductor layer 101, such as DTI (Deep Trench Isolation). In the embodiment in which the insulator extending through the semiconductor layer 101 is used, the semiconductor layer 101 may be divided into a plurality of portions by the isolation portion. Since the insulator is generally transparent, obliquely incident light readily enters an adjacent pixel. In such embodiment, therefore, it is possible to obtain the effect of reducing color mixing.

A plurality of transistors are arranged on the first face 1 of the semiconductor layer 101. The source and drain of each transistor are formed in the semiconductor layer 101, and the gate of each transistor is arranged on the first face 1 of the semiconductor layer 101 via a gate insulating film. The plurality of transistors can include, for example, a transfer transistor which forms, in the semiconductor layer 101, a channel for transferring charges accumulated in the photoelectric converter 102 to a floating diffusion. The plurality of transistors can also include a reset transistor for resetting the

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potential of the floating diffusion and an amplification transistor for outputting a signal corresponding to the potential of the floating diffusion to a vertical signal line.

FIG. 1 shows a gate 103 of the transfer transistor as an example of the plurality of transistors. The gate 103 can be made of, for example, polysilicon. The wiring structure WS is arranged on the side of the first face 1 of the semiconductor layer 101. The wiring structure WS can include an interlayer insulating film 119 which covers the first face 1 of the semiconductor layer 101 and the gates 103, wiring layers 108, 109, and 110, and an interlayer insulating film 105. The wiring layers 108, 109, and 110 are arranged in the interlayer insulating film 105. The interlayer insulating films 119 and 105 may be made of the same material or different materials. In an example, the interlayer insulating films 119 and 105 can be silicon oxide films. The gate 103 is connected to the wiring pattern of the wiring layer 108 via a contact plug 104.

In the example shown in FIG. 1, the wiring layers 108, 109, and 110 form the three-layer wiring structure WS. However, the number of wiring layers in the wiring structure WS is not limited to three. In the example shown in FIG. 1, the wiring layer 108 of the lowest layer (first layer) includes a plurality of reflection portions 106. Each reflection portion 106 has a reflection region RR. Part of light having entered through the microlens 113, which has not been absorbed by the photoelectric converter 102 of the semiconductor layer 101 enters the reflection region RR of the reflection portion 106, is reflected by the reflection region RR to return to the photoelectric converter 102, and is photoelectrically converted by the photoelectric converter 102. In this way, it is possible to improve the sensitivity by providing the reflection portions 106 on the side of the first face 1 of the semiconductor layer 101.

In a comparative example shown in FIG. 13, light 120 having obliquely passed through the photoelectric converter 102 enters the outer portion of the reflection portion 106, and is reflected by it. Light 121 reflected by the outer portion can enter the photoelectric converter 102 adjacent to the photoelectric converter 102 through which the light 120 has passed. This may cause color mixing.

In the first embodiment, as shown in FIG. 1, a plurality of light absorbing portions 107 respectively arranged around the reflection regions RR of the plurality of reflection portions 106 are provided in the wiring structure WS. Each light absorbing portion 107 can be arranged to surround the reflection region RR of the corresponding one of the plurality of reflection portions 106. Furthermore, an insulator portion INS is arranged to surround each of the plurality of light absorbing portions. The insulator portion INS can typically be part of the interlayer insulating film 105. Each light absorbing portion 107 can be made of, for example, an electrical conducting material. The interlayer insulating film 119 is arranged between the first face 1 of the semiconductor layer 101 and the plurality of reflection portions 106, the plurality of light absorbing portions 107, and the insulator portion INS.

The reflection regions RR of the reflection portions 106 and light incident surfaces 131 of the light absorbing portions 107 can be arranged on one virtual plane P. Each light incident surface 131 is one of the two surfaces of the corresponding light absorbing portion 107, which faces the first face 1 of the semiconductor layer 101 via the interlayer insulating film 119. The light absorbing portion 107 and reflection portion 106 can be arranged so that their outer edges coincide with each other. Note that the light absorbing portion 107 may absorb all light incident on it. Alternatively, the light absorbing portion 107 may absorb only part of

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light, which has reached there. Part of light, which has reached the light incident surface **131** of the light absorbing portion **107** from the side of the semiconductor layer **101**, may be reflected by the interface between the light absorbing portion **107** and the interlayer insulating film **119**, that is, the light incident surface **131**. Alternatively, light which has not been absorbed by the light absorbing portion **107** can be reflected by the surface on the opposite side of the light incident surface **131**, that is, the interface between the light absorbing portion **107** and the reflection portion **106**, returned to the light absorbing portion **107**, and then absorbed by it.

The reflectance of each of the plurality of light absorbing portions **107** is smaller than that of the reflection region **RR** of each of the plurality of reflection portions **106**. The light transmittance of each of the plurality of light absorbing portions **107** is smaller than that of the insulator portion **INS**. Decreasing the reflectance of the light absorbing portion **107** contributes to reducing color mixing. In terms of reduction of color mixing, therefore, the reflectance of the light absorbing portion **107** can be made as small as possible. Furthermore, decreasing the light transmittance of the light absorbing portion **107**, that is, increasing the light absorbing amount by the light absorbing portion **107** contributes to reducing color mixing. In terms of reduction of color mixing, therefore, the light transmittance of the light absorbing portion **107** can be made as small as possible.

In the example shown in FIG. 1, the reflection portions **106** are arranged in the wiring layer **108** of the lowest layer, that is, the first layer. However, as shown in FIG. 2, the reflection portions **106** may be arranged in another wiring layer, for example, the wiring layer **109** which is the wiring layer of the second layer. Alternatively, the reflection portions **106** may be arranged in the wiring layer **110** which is the wiring layer of the third layer.

FIG. 3 exemplifies the wiring structure **WS** taken along the virtual plane **P** shown in FIG. 2. The light absorbing portion **107** is arranged around the corresponding reflection region **RR**. Therefore, the reflection region **RR** is arranged in a region between the light absorbing portion **107** and the center of the reflection portion **106** on the virtual plane **P**. Referring to FIG. 3, the light absorbing portion **107** is arranged to surround the reflection region **RR** of the reflection portion **106**, and the insulator portion **INS** is arranged to surround the light absorbing portion **107**. In FIG. 3, a rectangular **114** schematically shows the region of one pixel. Note that in FIG. 3, the light absorbing portion **107** is arranged on the entire perimeter of the reflection region **RR**. However, the light absorbing portion **107** may be arranged to only partially surround the reflection region **RR**. For example, it is sometimes desirable to adjust the color mixing ratio with an adjacent pixel in a different direction. In such a case, the light absorbing portion **107** may be arranged in a portion near a pixel where it is preferable to reduce color mixing, and it may be omitted in the remaining portion. Alternatively, the light absorbing portion **107** may be intermittently arranged. A portion of the surface of the reflection portion **106** on the side of the semiconductor layer **101**, where the light absorbing portion **107** is not arranged, may be part of the reflection region **RR**.

The light absorbing portion **107** may be provided under the wiring pattern of a wiring layer **111** for communicating an electric signal, in addition to the reflection portion **106** which communicates no electric signal. As exemplified in FIG. 4, for example, the light absorbing portion **107** may be provided under a wiring pattern arranged on the wiring layer **108**.

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A method of manufacturing the solid-state image sensor **100** shown in FIG. 4 will be described below with reference to FIGS. **12A** to **12E**. In a process shown in FIG. **12A**, a p-type well region (not shown) is formed by implanting boron into an n-type semiconductor layer **101**. Furthermore, photoelectric converters **102** are formed by implanting phosphorus into the well region. After that, an oxide film (not shown) is formed on a first face **1** of the semiconductor layer **101**, and a polysilicon film is formed on the oxide film. Gates **103** of transfer transistors, and the gates of reset transistors and amplification transistors (non are shown) are formed by patterning the polysilicon film.

An interlayer insulating film **119** is formed on the first face **1** of the semiconductor layer **101** to cover the first face **1** and gates, and then the surface of the interlayer insulating film **119** is planarized. The interlayer insulating film **119** is preferably made of, for example, a material having transparency for visible light or infrared light. The interlayer insulating film **119** can be made of (a) silicon oxide, (b) silicon oxide doped with phosphorus, boron, nitrogen, fluorine, or the like, (c) silicon nitride, or (d) an acrylic resin.

Contact holes are formed to extend through the interlayer insulating film **119**. An electrical conducting material film is formed in the contact holes and on the interlayer insulating film **119**. The electrical conducting material film is polished, thereby forming contact plugs **104**.

In a process shown in FIG. **12B**, a light absorbing material film is formed to cover the interlayer insulating film **119**, and then patterned, thereby forming a light absorbing material pattern **107'**. The light absorbing material pattern **107'** has openings **OP** in regions in each of which a reflection region **RR** should be formed. Note that the light absorbing material film (light absorbing material pattern **107'**) is a film (pattern) for forming light absorbing portions **107**, and its reflectance is smaller than that of the reflection region **RR** of each reflection portion **106** and its transmittance is smaller than that of an insulator portion **INS**. The light absorbing material film (light absorbing material pattern **107'**) can be made of, for example, an electrical conducting material such as titanium nitride (**TiN**) or silicon carbide (**SiC**). The light absorbing material film (light absorbing material pattern **107'**) may be formed from, for example, a multilayered film consisting of a titanium nitride (**TiN**) film and silicon carbide (**SiC**) film. The light absorbing material film may be made of a material used for a barrier metal.

In a process shown in FIG. **12C**, a reflective material film **106'** is formed to cover the interlayer insulating film **119** and light absorbing material pattern **107'**. Note that the reflective material film **106'** can be considered as a film for forming a wiring layer **108** including a plurality of reflection portions **106**, that is, a wiring material film.

The reflective material film **106'** can be made of an electrical conducting material. The electrical conducting material is preferable as a material having an appropriate reflectance and conductivity. The reflective material film **106'** can contain aluminum, copper, gold, tungsten, titanium, or tantalum as a main component. If a material having a large diffusion coefficient such as copper is used for the reflective material film **106'**, it is preferable to stack a diffusion preventing film to cover the reflective material film **106'**. For the diffusion preventing film, for example, silicon nitride or silicon carbide can be used. The reflection portions **106** and a portion of the wiring layer **108** other than the reflection portions **106** may be formed using different materials in different processes. In this case, the reflection portions **106** may be made of a material having low conduc-

tivity, and the portion of the wiring layer **108** other than the reflection portions **106** may be made of a material having low reflectance.

In a process shown in FIG. **12D**, the reflective material film **106'** is patterned by etching so that a plurality of reflection portions **106** are formed. Furthermore, a portion of the light absorbing material pattern **107'** which is exposed by etching the reflective material film **106'** is etched. With this process, a plurality of reflection portions **106** and a plurality of light absorbing portions **107** are formed.

In a process shown in FIG. **12E**, an interlayer insulating film **105** is formed to cover the interlayer insulating film **119** and the plurality of reflection portions **106**, and then planarized, thereby forming a wiring layer **109** on it. Similarly, an interlayer insulating film **105** is formed to cover the wiring layer **109**, and then planarized, thereby forming a wiring layer **110** on it. In this way, a wiring structure **WS** is formed. The interlayer insulating film **105** can be, for example, a silicon oxide film.

After that, a support substrate (not shown) may be bonded to the surface side of the wiring structure **WS**. The support substrate is useful to improve the mechanical strength. For example, a silicon substrate or the like can be used as the support substrate.

A second face **2** of the semiconductor layer **101** is polished and planarized. On the side of the second face **2**, a planarizing layer **112**, a color filter (not shown), and microlenses **113** can be formed, as needed.

A solid-state image sensor **100** according to the second embodiment of the present invention will be described below with reference to FIG. **5**. Note that points not mentioned in the second embodiment can comply with the first embodiment. In the second embodiment, a plurality of reflection portions **106** are formed as part of a wiring pattern for communicating an electric signal. For example, each reflection portion **106** can be formed as part of a wiring pattern connected to a gate **103**, source, or drain of a transfer transistor. Alternatively, each reflection portion **106** can be formed as part of a wiring pattern connected to the gate, source, or drain of a reset transistor or amplification transistor. Or, each reflection portion **106** can be formed as part of a vertical signal line to which a signal is output from a pixel. Or, each reflection portion **106** can be formed as part of a wiring pattern for supplying a reference ground voltage to a pixel.

In the second embodiment, it is possible to improve the degree of freedom of wiring by forming each reflection portion **106** as part of a wiring pattern for communicating an electric signal. Each reflection portion **106** may be formed as part of a wiring pattern for communicating an electric signal in a wiring layer other than a wiring layer **108** of a first layer, for example, a wiring layer **109** of a second layer or a wiring layer **110** of a third layer.

A solid-state image sensor **100** according to the third embodiment of the present invention will be described below with reference to FIGS. **6A** and **6B**. Note that points not mentioned in the third embodiment can comply with at least one of the first and second embodiments.

A plurality of photoelectric converters **102** include a first photoelectric converter **102** on which light of a first wavelength range is incident, a second photoelectric converter **102** on which light of a second wavelength range is incident, and a third photoelectric converter **102** on which light of a third wavelength range is incident. Note that a wavelength within the second wavelength range is shorter than that within the first wavelength range, and a wavelength within the third wavelength range is shorter than that within the

second wavelength range. More specifically, the first wavelength range can be a red (R) wavelength range, the second wavelength range can be a green (G) wavelength range, and the third wavelength range can be a blue (B) wavelength range. Referring to FIGS. **6A** and **6B**, reference symbols R, G, and B denote pixels for detecting light of the red (R) wavelength range, light of the green (G) wavelength range, and light of the blue (B) wavelength range, respectively.

In the third embodiment, a plurality of reflection portions **106** are arranged for only the first photoelectric converter (R) or only the first photoelectric converter (R) and third photoelectric converter (G). That is, in the third embodiment, the reflection portions **106** are respectively provided for some of the plurality of photoelectric converters **102**. Note that in the first embodiment, the reflection portions **106** are respectively provided for all of the plurality of photoelectric converters **102**. From the first and third embodiments, it is apparent that the reflection portions **106** need only be provided for at least some of the plurality of photoelectric converters **102**.

The ratio at which light incident on a second face **2** of a semiconductor layer **101** is absorbed by the semiconductor layer **101** until it reaches a first face **1** becomes smaller as the wavelength of the light is longer. That is, the ratios of light beams which reach the first face **1** are larger in the order of a red (R) pixel, green (G) pixel, and blue (B) pixel. That is, the effect of improving the sensitivity and reducing color mixing by providing the reflection portions **106** and light absorbing portions **107** is largest in a red (R) pixel. As shown in FIG. **6A**, therefore, the reflection portion **106** and light absorbing portion **107** may be provided in only a red (R) pixel. Alternatively, as shown in FIG. **6B**, the reflection portions **106** and light absorbing portions **107** may be provided in only a red (R) pixel and green (g) pixel.

The third embodiment is useful when the layouts of a plurality of pixels are different from each other, and it is difficult to provide reflection portions **106** and light absorbing portions **107** in all the pixels, for example, when a plurality of photoelectric converters **102** share a floating diffusion.

A solid-state image sensor **100** according to the fourth embodiment of the present invention will be described below with reference to FIGS. **7** to **11B**. Note that points not mentioned in the fourth embodiment can comply with at least one of the first to third embodiments. In the solid-state image sensor **100** according to the fourth embodiment, the relative position between a photoelectric converter **102** and a corresponding reflection region **RR** and light absorbing portion **107** is determined depending on the position of the photoelectric converter **102** in a semiconductor layer **101**.

When the position of the photoelectric converter **102** in the semiconductor layer **101** changes, the direction of light which passes through a first face **1** of the semiconductor layer **101** also changes. It is preferable to change the shape of the reflection region **RR** and light absorbing portions **107** corresponding to the photoelectric converter **102** in accordance with the position of the photoelectric converter **102** in the semiconductor layer **101**. This can be done so that sensitivity and color mixing nonuniformities over the whole imaging region formed by the array of a plurality of photoelectric converters **102** fall within tolerance ranges, respectively.

The fourth embodiment will be explained below based on a practical example with reference to FIGS. **7** to **11B**. FIG. **7** shows the imaging region formed by the array of the plurality of photoelectric converters **102**. Referring to FIG. **7**, reference symbols PU, PUR, PL, PC, PR, PDL, and PD

denote the positions of the photoelectric converters **102** (pixels) in the imaging region. Each of FIGS. **8A** and **8B** schematically shows reflection regions **RR** (reflection portions **106**), light absorbing portions **107**, and an insulator portion **INS** (interlayer insulating film **105**) of four pixels arranged at each of the positions **PU** and **PUR** shown in FIG. **7**. Each of FIGS. **9A** to **9C** schematically shows reflection regions **RR** (reflection portions **106**), light absorbing portions **107**, and an insulator portion **INS** (interlayer insulating film **105**) of four pixels arranged at each of the positions **PL**, **PC**, and **PR** shown in FIG. **7**. Each of FIGS. **10A** and **10B** schematically shows reflection regions **RR** (reflection portions **106**), light absorbing portions **107**, and an insulator portion **INS** (interlayer insulating film **105**) of four pixels arranged at each of the positions **PDL** and **PD** shown in FIG. **7**. Each of FIGS. **11A** and **11B** is a sectional view showing pixels arranged at each of the positions **PL** and **PR** shown in FIG. **7** taken along a cut surface parallel to the **x** direction.

In a pixel **114** arranged in the outer portion of a pixel region, the width of the light absorbing portion **107** is larger on the outer edge side of the pixel region than on the center side of the pixel region. Accordingly, the shape of the reflection region **RR** changes. In a portion on the center side of the pixel region, the light absorbing portion **107** may be omitted and the edge of the reflection region **RR** may coincide with the boundary of an insulator layer.

As an application of the solid-state image sensor according to each of the aforementioned embodiments, a camera incorporating the solid-state image sensor will be exemplarily described below. The camera conceptually includes not only a device whose principal purpose is photographing but also a device (for example, a personal computer or portable terminal) additionally provided with a photographing function. The camera includes the solid-state image sensor according to the present invention, which has been exemplified in the above embodiments, and a processing unit for processing a signal output from the solid-state image sensor. The processing unit can include, for example, an A/D converter, and a processor for processing digital data output from the A/D converter.

While the present invention has been described with reference to exemplary embodiments, it is to be understood that the invention is not limited to the disclosed exemplary embodiments. The scope of the following claims is to be accorded the broadest interpretation so as to encompass all such modifications and equivalent structures and functions.

This application claims the benefit of Japanese Patent Application No. 2012-248709, filed Nov. 12, 2012, which is hereby incorporated by reference herein in its entirety.

What is claimed is:

1. A solid-state image sensor comprising:

a semiconductor layer having a first face and a second face, a plurality of photoelectric converters being arranged in the semiconductor layer;

a plurality of conductive portions arranged at a side of the first face;

a plurality of lenses arranged at a side of the second face; an interlayer insulator film disposed between the plurality of conductive portions and the semiconductor layer; and

a barrier metal portion disposed between a conductive portion of the plurality of conductive portions and the interlayer insulator film,

wherein a surface of the conductive portion at a side of the semiconductor layer has a first region and a second region out of the first region, the first region and the

second region forming a stepped shape in the surface of the conductive portion, and

wherein the barrier metal portion has an opening through which the first region of the conductive portion faces the semiconductor layer through the interlayer insulator film so that a part of the conductive portion is provided in the opening, and the barrier metal portion is disposed between the second region and the interlayer insulator film.

2. The solid-state image sensor according to claim 1, wherein the conductive portion is formed of a material selected from a group consisting of aluminum, copper, gold, tungsten, titanium and tantalum.

3. The solid-state image sensor according to claim 1, wherein the barrier metal portion is formed of a material selected from a group consisting of a titanium nitride and a silicon carbide.

4. The solid-state image sensor according to claim 1, further comprising a plurality of barrier metal portions including the barrier metal portion, the plurality of barrier metal portions being separated from each other by an insulator portion.

5. The solid-state image sensor according to claim 1, wherein the first region of the conductive portion is in contact with the interlayer insulator film.

6. The solid-state image sensor according to claim 1, wherein a reflectance of a material of the barrier metal portion is smaller than a reflectance of a material of the first region.

7. The solid-state image sensor according to claim 1, wherein the conductive portion is formed as a part of a wiring pattern for communicating an electric signal.

8. A solid-state image sensor, comprising:

a semiconductor layer having a first face and a second face; and

a wiring structure arranged on the first face,

wherein a plurality of photoelectric converters are arranged in the semiconductor layer,

wherein light from an object is incident on the photoelectric converters through the second face,

wherein the wiring structure includes a conductive portion and a barrier metal portion disposed between the conductive portion and the semiconductor layer, and

wherein the barrier metal portion has an opening through which a reflection region of the conductive portion is provided

wherein the plurality of photoelectric converters include a first photoelectric converter on which light of a first wavelength range is incident, a second photoelectric converter on which light with a wavelength within a second wavelength range, that is shorter than the first wavelength range, is incident, and a third photoelectric converter on which light with a wavelength within a third wavelength range, that is shorter than the second wavelength range, is incident, and

wherein the conductive portion and the barrier metal portion are provided for only the first photoelectric converter or only the first photoelectric converter and the second photoelectric converter.

9. A camera comprising:

a solid-state image sensor according to claim 1; and

a processor which processes a signal output from the solid-state image sensor.

10. A solid-state image sensor comprising:

a semiconductor layer having a first face and a second face, a plurality of photoelectric converters being arranged along the first face in the semiconductor layer;

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a plurality of first patterns arranged on and along the first face;
 a plurality of lenses arranged at a side of the second face;
 an interlayer insulator film disposed between the plurality of first patterns and the semiconductor layer; and
 a second pattern disposed between a first pattern of the plurality of first patterns and the interlayer insulator film,
 wherein a surface of the first pattern at a side of the semiconductor layer has a first region and a second region out of the first region, the first region and the second region forming a stepped shape in the surface of the first pattern, and
 wherein the second pattern has an opening through which the first region of the first pattern faces the semiconductor layer through the interlayer insulator film so that a part of the first pattern is provided in the opening, and the second pattern is disposed between the second region and the interlayer insulator film,
 wherein the first pattern is formed of a material selected from a group consisting of aluminum, copper, gold, tungsten, titanium and tantalum, and the second pattern is formed of a titanium nitride.

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11. A camera comprising:
 a solid-state image sensor according to claim **8**; and
 a processor which processes a signal output from the solid-state image sensor.

12. A camera comprising:
 a solid-state image sensor according to claim **10**; and
 a processor which processes a signal output from the solid-state image sensor.

13. The solid-state image sensor according to claim **1**, wherein the interlayer insulator film is formed of silicon oxide.

14. The solid-state image sensor according to claim **10**, wherein the interlayer insulator film is formed of silicon oxide.

15. The solid-state image sensor according to claim **10**, wherein the first region of the first pattern is in contact with the interlayer insulator film.

16. The solid-state image sensor according to claim **5**, wherein the first region of the conductive portion is in contact with the barrier metal portion.

17. The solid-state image sensor according to claim **15**, wherein the second region of the first pattern is in contact with the second pattern.

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